

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
40V	30mΩ @ V _{GS} = 10V	13.8A
	54mΩ @ V _{GS} = 4.5V	10.3A

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

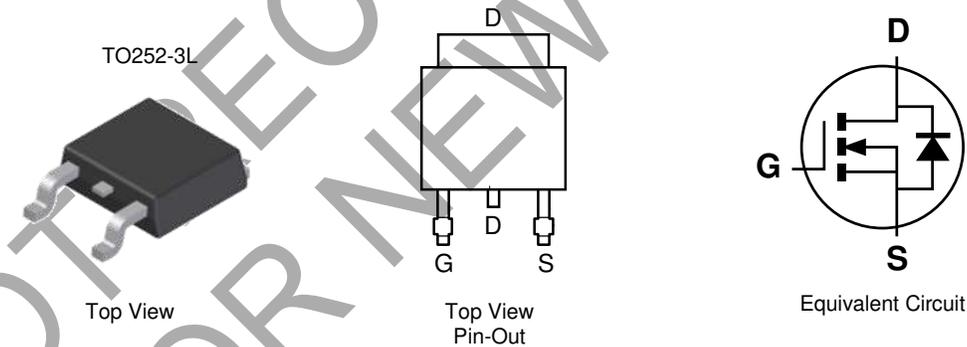
- Backlighting
- DC-DC converters
- Power management functions

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.** <https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: TO252-3L
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Weight: 0.33 grams (Approximate)

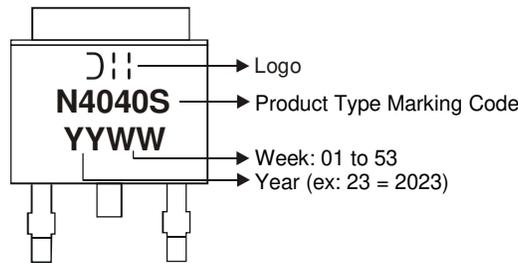


Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN4040SK3-13	TO252-3L	2500	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	40	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	6.0	A
		T _A = +70°C		4.8	
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	9.3	A
		T _A = +70°C		7.4	
Continuous Drain Current (Note 6) V _{GS} = 10V	t ≤ 10s	T _A = +25°C	I _D	13.8	A
		T _A = +70°C		11.0	
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _A = +25°C	I _D	6.9	A
		T _A = +70°C		5.5	
Continuous Drain Current (Note 6) V _{GS} = 4.5V	t ≤ 10s	T _A = +25°C	I _D	10.3	A
		T _A = +70°C		8.2	
Pulsed Drain Current (Note 7)			I _{DM}	50	A

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	P _D	1.71	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	R _{θJA}	72.9	°C/W
Power Dissipation (Note 6)	P _D	4.1	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	R _{θJA}	30.8	°C/W
Power Dissipation (Note 6) t ≤ 10s	P _D	8.9	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6) t ≤ 10s	R _{θJA}	14	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
- Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
 - Device mounted on 2" x 2" FR-4 PCB with high coverage 2oz. copper, single sided.
 - Repetitive rating, pulse width limited by junction temperature.

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	—	—	1.0	μA	$V_{DS} = 40V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.8	2.3	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	20	30	m Ω	$V_{GS} = 10V, I_D = 12A$
		—	43	54		$V_{GS} = 4.5V, I_D = 6A$
Forward Transfer Admittance	$ Y_{fs} $	—	11	—	S	$V_{DS} = 5V, I_D = 12A$
Diode Forward Voltage	V_{SD}	—	0.76	1.0	V	$V_{GS} = 0V, I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	945	—	pF	$V_{DS} = 20V, V_{GS} = 0V$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	69	—		
Reverse Transfer Capacitance	C_{rss}	—	58	—		
Gate Resistance	R_g	—	1.45	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1\text{MHz}$
Total Gate Charge $V_{GS} = 4.5V$	Q_g	—	8.4	—	nC	$V_{GS} = 4.5V, V_{DS} = 20V$ $I_D = 12A$
Total Gate Charge $V_{GS} = 10V$	Q_g	—	18.6	—		
Gate-Source Charge	Q_{gs}	—	3.3	—		
Gate-Drain Charge	Q_{gd}	—	2.2	—		
Turn-On Delay Time	$t_{D(ON)}$	—	6.4	—	ns	$V_{GS} = 10V, V_{DS} = 20V$ $R_L = 1.6\Omega, R_g = 3\Omega$
Turn-On Rise Time	t_r	—	9.7	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	19.8	—	ns	
Turn-Off Fall Time	t_f	—	3.1	—	ns	

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to production testing.

NOT RECOMMENDED FOR NEW DESIGN

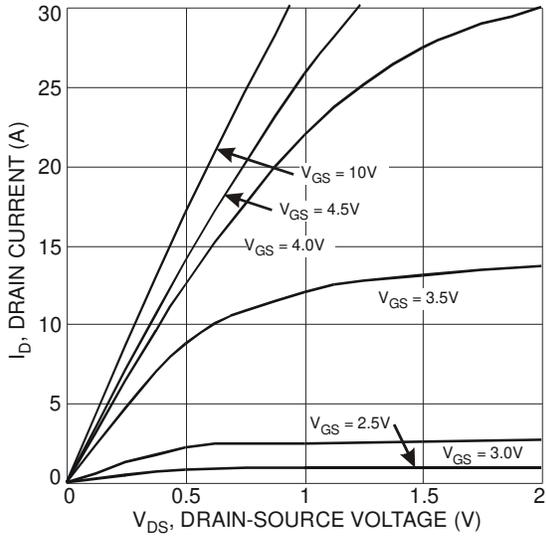


Fig. 1 Typical Output Characteristic

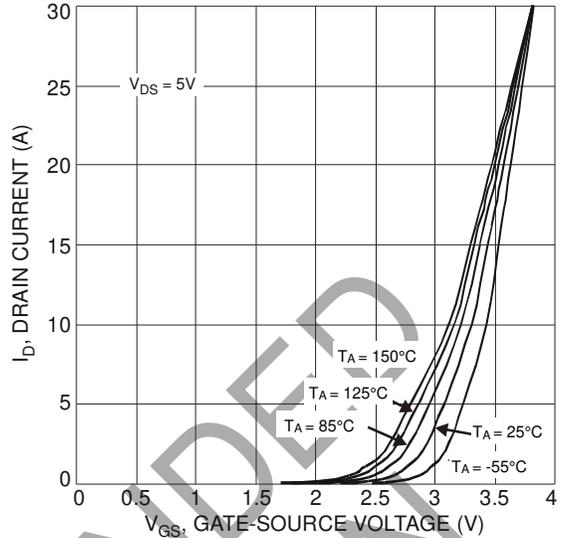


Fig. 2 Typical Transfer Characteristic

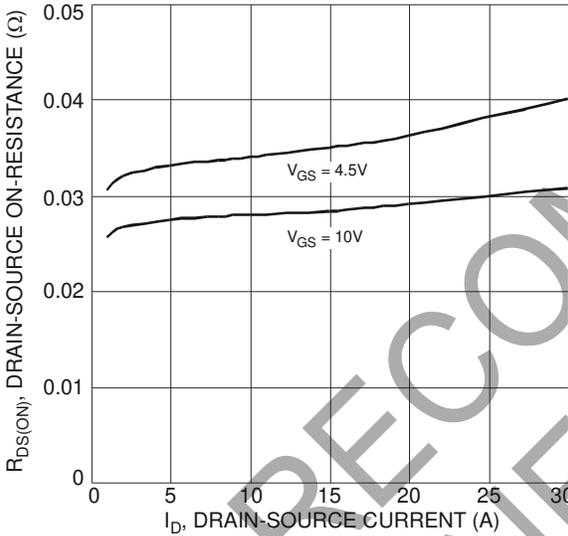


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

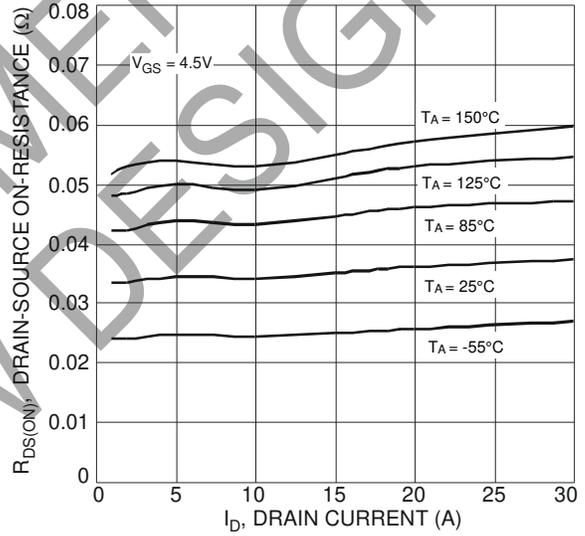


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

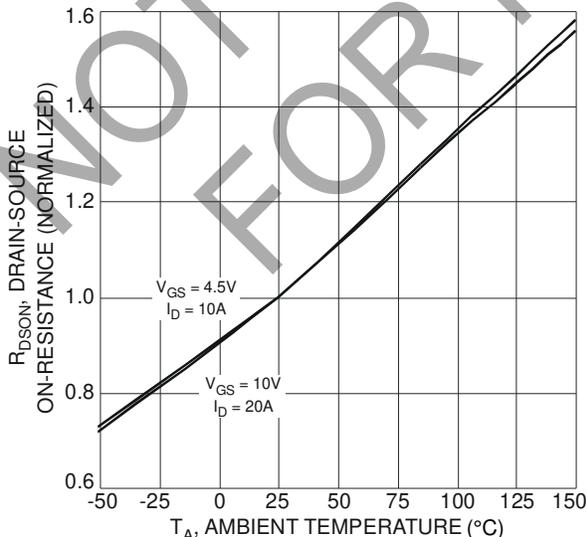


Fig. 5 On-Resistance Variation with Temperature

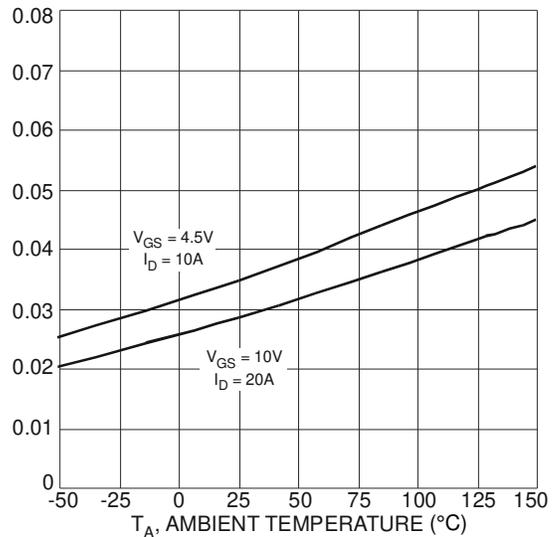


Fig. 6 On-Resistance Variation with Temperature

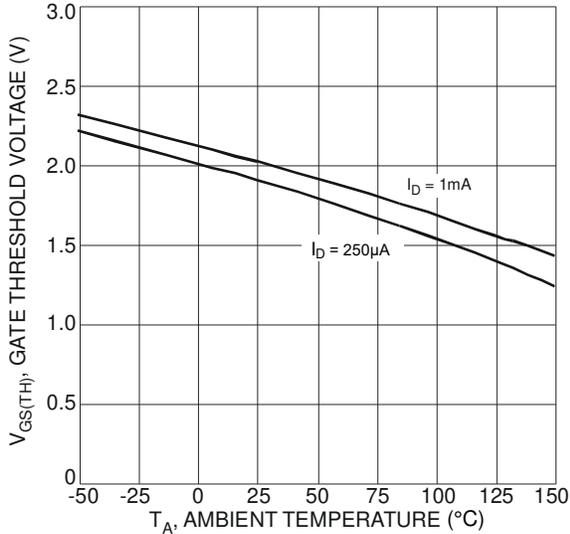


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

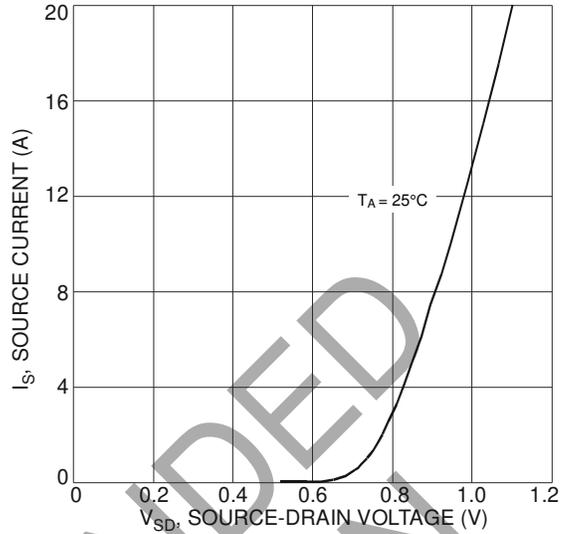


Fig. 8 Diode Forward Voltage vs. Current

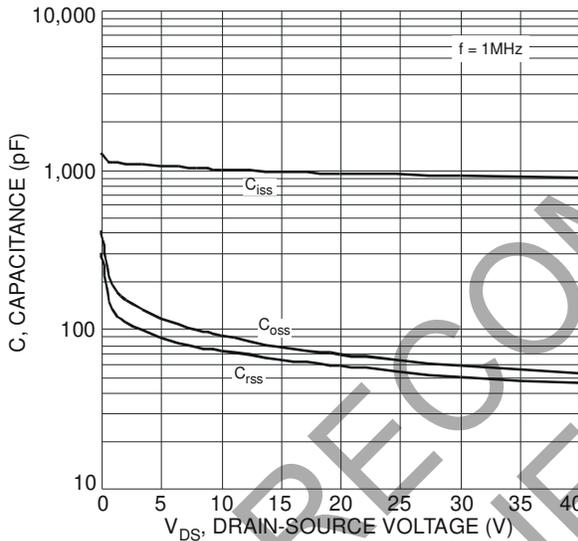


Fig. 9 Typical Total Capacitance

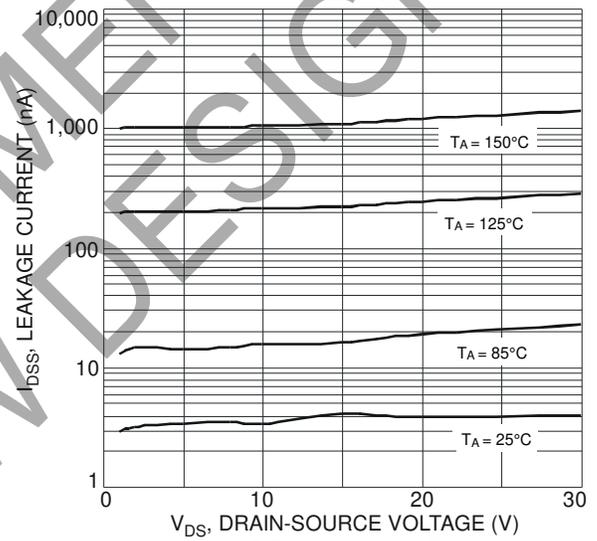


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

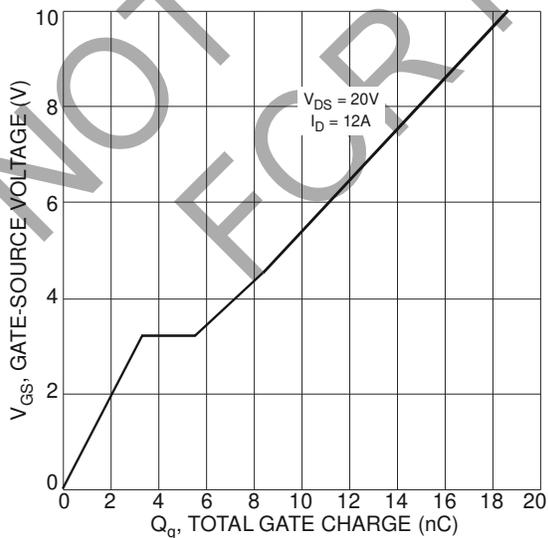


Fig. 11 Gate-Charge Characteristics

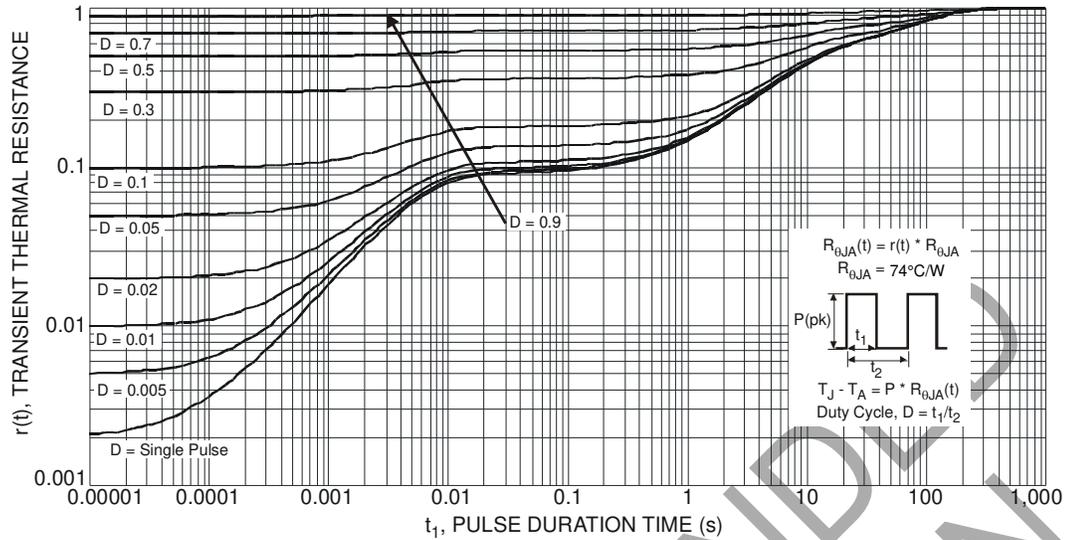


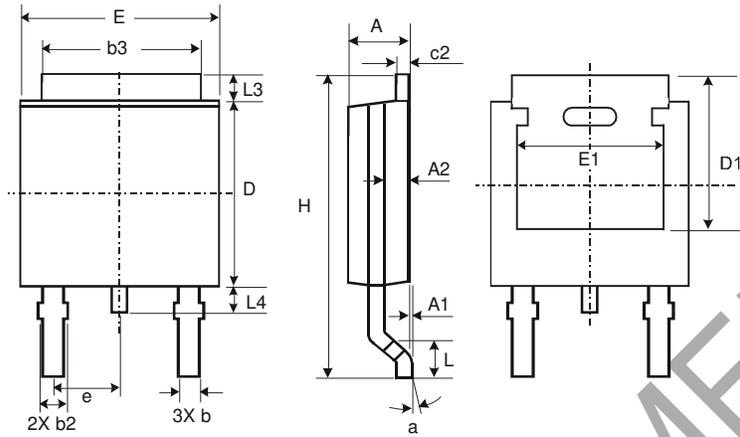
Fig. 12 Transient Thermal Response

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Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252-3L

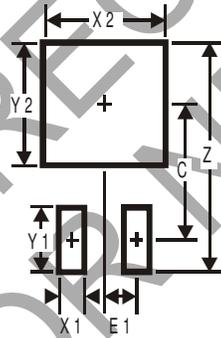


TO252-3L			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c2	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252-3L



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
C	6.9
E1	2.3

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